

## Monday June 5<sup>th</sup>

19h00 - 21h00	<b>Welcome Reception</b>
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## Tuesday June 6<sup>th</sup>

08:00 - 08:30	<b>Opening Ceremony</b>	
08:30 - 10:00	<b>PLENARY SESSION 1</b>	
	<p><b>Tu-PS1.1</b> 08:30-09:15: <a href="#">M. Kushimoto</a>, CW operation of UVC lasers</p> <p><b>Tu-PS1.2</b> 09:15-10:00: <a href="#">J. Kim</a>, 2D materials for UV application</p>	
10:00 - 10:30	<b>Coffee break</b>	
10:30 - 12:30	<p style="text-align: center;"><b>A1 – Oxides</b></p> <p><b>Tu-A1.1</b> 10:30-10:55: <a href="#">E. Chikoidze</a>, Ultra Wide Band Gap Gallia and Zinc Gallate electronic properties</p> <p><b>Tu-A1.2</b> 10:55-11:20: <a href="#">T. Onuma</a>, Far UV optical properties of MgO homoepitaxial and Zn doped MgO films prepared by mist chemical vapor deposition method</p> <p><b>Tu-A1.3</b> 11:20-11:45: <a href="#">G. Fanchini</a>, Defect-Related Optoelectronic and Magnetic Properties of Nanostructured Nickel Oxides as Charge Transport Layers in Organic Photovoltaics</p> <p><b>Tu-A1.4</b> 11:45-12:00: <a href="#">Z. Liu</a>, Ultrathin and Freestanding Ga<sub>2</sub>O<sub>3</sub> Membrane Developed by Thermal Mismatch Engineering for Vertical Electronics</p> <p><b>Tu-A1.5</b> 12:00-12:15: <a href="#">Y. Zhang</a>, Beta-Gallium Oxide nanowire-based electronic devices and its low frequency noise analysis</p> <p><b>Tu-A1.6</b> 12:15-12:30: <a href="#">D. Rogers</a>, High Gain UVC (Al)Ga<sub>2</sub>O<sub>3</sub> Photodetectors with Tunable Spectral Response and Extreme Solar Blindness</p>	<p style="text-align: center;"><b>B1 UV Phot/UV Char</b></p> <p><b>Tu-B1.1</b> 10:30-10:55: <a href="#">B. Gil</a>, The Optical Properties of Various Polytypes of sp<sup>2</sup>-bonded Boron Nitride</p> <p><b>Tu-B1.2</b> 10:55-11:20: <a href="#">Y. Auaq</a>, Cathodoluminescence excitation spectroscopy: revealing the excitation pathways in the nanometer scale</p> <p><b>Tu-B1.3</b> 11:20-11:45: <a href="#">R. Butte</a>, Polaritonic effects in III-nitride planar waveguides and microring resonators</p> <p><b>Tu-B1.4</b> 11:45-12:00: <a href="#">B. Szafranski</a>, Time-resolved cathodoluminescence spectroscopy of oxygen related defects in AlN layers</p> <p><b>Tu-B1.5</b> 12:00-12:15: <a href="#">K. Korona</a>, Time-Resolved UV Photoluminescence of Color Centers in MOCVD-Grown Boron Nitride</p> <p><b>Tu-B1.6</b> 12:15-12:30: <a href="#">P. Gonzalez-Izquierdo</a>, Kelvin Probe Force Microscopy under variable illumination: a novel technique to unveil charge carrier dynamics in (Al/In/Ga)N</p>
12:30 - 13:30	<b>Lunch / Poster session</b>	
13:30 - 15:00	<p style="text-align: center;"><b>A2 2D/Nano</b></p> <p><b>Tu-A2.1</b> 13:30-13:55: <a href="#">J. K Kim</a>, Growth of hexagonal boron nitride by MOCVD for DUV applications</p> <p><b>Tu-A2.2</b> 13:55-14:10: <a href="#">A. Rousseau</a>, Optical Characterization Of Exfoliated Monolayer Boron Nitride By Means Of Hyperspectral Microscopy In The Deep-UV</p> <p><b>Tu-A2.3</b> 14:10-14:25: <a href="#">V. Ottapilakkal</a>, MOVPE Growth of Thin hexagonal Boron Nitride on Patterned Epigraphene</p> <p><b>Tu-A2.4</b> 14:25-14:40: <a href="#">J. Rogoza</a>, Fabrication of hexagonal boron nitride membranes on germanium for Raman signal enhancement</p>	<p style="text-align: center;"><b>B2 UV emitters</b></p> <p><b>Tu-B2.1</b> 13:30-13:55: <a href="#">M. Iwaya</a>, Toward enhancement of light output power of AlGaIn-based UV-B laser diodes</p> <p><b>Tu-B2.2</b> 13:55-14:10: <a href="#">E. Torres-Vasquez</a>, Resonant-cavity UVB LEDs with tunnel-junctions and all-dielectric DBRs</p> <p><b>Tu-B2.3</b> 14:10-14:25: <a href="#">R. Dupuis</a>, Crack suppression of high Al-mole-fraction AlGaIn layers on patterned GaN substrates for ultraviolet light emitting diodes and laser diodes</p> <p><b>Tu-B2.4</b> 14:25-14:40: <a href="#">J. Rass</a>, UV micro-LEDs and micro-LED arrays for high efficiency and new applications</p> <p><b>Tu-B2.5</b> 14:40-14:55: <a href="#">E. Akar</a>, GaN Nanowire Ensembles Ultraviolet Photodetectors based on Photoconductors and Schottky Photodiode</p>
15:00 - 15:30	<b>Coffee break</b>	
15:30 - 17:30	<p style="text-align: center;"><b>A3 AlGaIn/AlN</b></p> <p><b>Tu-A3.1</b> 15:30-15:55: <a href="#">S. Hagedorn</a>, Fabrication of high-quality AlN and AlGaIn templates</p> <p><b>Tu-A3.2</b> 15:55-16:20: <a href="#">K. Uesugi</a>, Homo-epitaxial growth on high temperature annealed AlN template and device applications</p> <p><b>Tu-A3.3</b> 16:20-16:35: <a href="#">Y. Guo</a>, Improved crystallinity and surface morphology of a-plane AlN grown on r-sapphire by pulsed-flow Mode MOVPE</p> <p><b>Tu-A3.4</b> 16:35-16:50: <a href="#">C. Margenfeld</a>, Point Defect Engineering for Enhanced Dislocation Annihilation During High-Temperature Annealing of AlN Templates</p> <p><b>Tu-A3.5</b> 16:50-17:05: <a href="#">P. Vuong</a>, Investigation of p-type doping in BAlN alloys for deep ultraviolet optoelectronics</p> <p><b>Tu-A3.6</b> 17:05-17:30: <a href="#">S. Zhao</a>, AlGaIn nanowire LEDs / MBE for UV sources</p>	<p style="text-align: center;"><b>B3 2D/Nano</b></p> <p><b>Tu-B3.1</b> 15:30-15:55: <a href="#">D. Cai</a>, 2.5-inch hexagonal boron nitride for van der Waals heteroepitaxy and p/n type conduction</p> <p><b>Tu-B3.2</b> 15:55-16:20: <a href="#">H. Sun</a>, Deep ultraviolet micro LEDs</p> <p><b>Tu-B3.3</b> 16:20-16:45: <a href="#">B. Daudin</a>, AlN nanowire LEDs</p> <p><b>Tu-B3.4</b> 16:45-17:00: <a href="#">Z. Liu</a>, Principles for 2D Material Assisted Nitrides Epitaxial Growth</p> <p><b>Tu-B3.5</b> 17:00-17:15: <a href="#">N. Bernhardt</a>, The pursuit of deep-UV defect emitters in 2D hBN</p> <p><b>Tu-B3.6</b> 17:15-17:30: <a href="#">T. Wei</a>, Graphene-assisted growth of single crystalline GaN on SiO<sub>2</sub>/Si(100) for monolithic optoelectronic integration and flexible devices</p>
17:30 - 17:45	<b>Coffee break</b>	

Tuesday June 6<sup>th</sup>

**Poster Session**

**2D/Nano**

- Tu-P1** A. Zaiter, Investigating the role of h-BN on the growth of AlN by MBE
- Tu-P2** L. Janicki, Dodecagonal III-nitride microrods – a basis for future UV devices
- Tu-P3** I. Pugazhendi, Hybrid CsPbBr<sub>3</sub> quantum dots decorated two dimensional MoO<sub>3</sub> nanosheets photodetectors with enhanced performance
- Tu-P4** L. Wang, Threading dislocation defects effecting on the optical gain in GaN terahertz quantum cascade laser
- Tu-P5** K. Korona, Kinetics of UV luminescence of LED structures embedded in GaN/AlGaN nanowires
- Tu-P6** A. Kaur, Formation of Two Dimensional Electron Gas (2DEG) in Wedge Shaped Nanostructures of GaN: Validation of the Theoretical Model
- Tu-P7** V. Ottapilakkal, Growth of Thin BN films on C face Epigraphene using MOVPE
- Tu-P8** V. Ottapilakkal, Thermal Stability of Thin hexagonal boron Nitride Grown by MOVPE on Epigraphene
- Tu-P9** R. He, Wafer-Scale Efoliation of AlN Film via hexagonal BN-Assisted van der Waals Epitaxy for Deep-Ultraviolet Light-Emitting Diodes
- Tu-P10** F.Z. Tijent, Hydrogen production and storage using hexagonal boron nitride (h-BN)

**AlN/AlGaN**

- Tu-P11** L. Peters, Sublimation Behavior of AlN in Nitrogen and Argon at Conditions Used for High-Temperature Annealing
- Tu-P12** D. Lee, The effect of thermally treated AlN powder on defect formation of AlN single crystals
- Tu-P13** Z. Kushitashvili, UV Stimulated Technology Receiving Nanoscale III- Nitrides
- Tu-P14** A. Kaminska, Influence of strain on the excitonic bandgap of AlN epitaxial layers grown on Si and sapphire substrates
- Tu-P15** H. Lu, *Linearity Improvements of Sub-micrometer AlN/GaN-based Heterostructure for Millimeter-wave Applications (To be confirmed)*

**Oxides**

- Tu-P16** T. Hubacek, Surface morphology of diamond grown on III-nitrides layers
- Tu-P17** J. Batysta, Optical properties of diamond layers grown on III-nitrides
- Tu-P18** E. Butanovs, The Effect of a Nucleation Layer on Morphology and Grain Size in MOCVD-Grown  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> Thin Films on C-Plane Sapphire
- Tu-P19** Z. Chi, Zn Doping Effect on Electrical Transport Properties in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>
- Tu-P20** I. Zhelezova, Vacancy defects in Si doped  $\beta$ -(Al,Ga)<sub>2</sub>O<sub>3</sub>

**UV Phot/UV Emit.**

- Tu-P21** S. Arora, Electroluminescence Study of Spatially Indirect Interfacial Excitons in n-ZnO/p-GaN Heterostructures
- Tu-P22** J. Yoshinaga, Epitaxial growth of AlGaIn-based deep-ultraviolet light-emitting diodes on a 6-inch sputter-annealed AlN template by using MOCVD system for mass production
- Tu-P23** R. Ren, *Lasing threshold reduction of AlGaIn based UV-C laser diodes on strain relaxed lower cladding layer (To be confirmed)*
- Tu-P24** R. Hernandez, Flexible nanowire UV LEDs
- Tu-P25** F. Dominec, Roughness and doping effects on p-diamond/n-nitride heterointerface diodes

17:45  
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19:30

## Wednesday June 7<sup>th</sup>

08:30 – 10:00	<b>PLENARY SESSION 2</b>	
	<p><b>We-PS2.1 08:30-09:15:</b> <a href="#">H. Miyake</a>, Sputtering growth of AlN for high quality template and its application for UV LEDs</p> <p><b>We-PS2.2 09:15-10:00:</b> <a href="#">M. Strassburg</a>, UV-C LEDs – from development to todays and future applications</p>	
10:00 – 10:30	<b>Coffee break</b>	
10:30 – 12:30	<p style="text-align: center;"><b>A4 UV Phot/UV Char</b></p> <p><b>We-A4.1 10:30-10:45:</b> <a href="#">N. Nikitskiy</a>, Anomalous temperature dependence of the emission properties of (Al,Ga)N quantum dots emitting in the UV range</p> <p><b>We-A4.2 10:45-11:00:</b> <a href="#">A. Perepeliuc</a>, On the origin of giant persistent photoconductivity in hexagonal boron nitride</p> <p><b>We-A4.3 11:00-11:15:</b> <a href="#">J. Plo</a>, Isotopic composition-dependent deep level emission in hexagonal boron nitride</p> <p><b>We-A4.4 11:15-11:30:</b> <a href="#">P. Shen</a>, A high-responsivity solar-blind photodetecting paper with sandwiched ZnO nanoarray/hexagonal boron nitride monolayer</p> <p><b>We-A4.5 11:30-11:45:</b> <a href="#">P. Gao</a>, <i>Atomic Structure and Phonon Transport Behavior of Heterointerfaces in AlN-based Films (To be confirmed)</i></p> <p><b>We-A4.6 11:45-12:00:</b> <a href="#">G. Alvarez</a>, Cross-plane thermal conductivity of h-BN grown by pulsed laser deposition</p> <p><b>We-A4.7 12:00-12:25:</b> <a href="#">R. Katayama</a>, <i>Deep UV light generation by nitride-based second harmonic generation wavelength conversion devices (To be confirmed)</i></p>	<p style="text-align: center;"><b>B4 UV emitters</b></p> <p><b>We-B4.1 10:30-10:55:</b> <a href="#">M. Dawson</a>, Optical Wireless Communication with Ultraviolet micro-LEDs</p> <p><b>We-B4.2 10:55-11:10:</b> <a href="#">T. Wernicke</a>, Analysis of the radiative recombination efficiency, carrier injection efficiency and light extraction efficiency in 265 nm LEDs</p> <p><b>We-B4.3 11:10-11:25:</b> <a href="#">D. Apaydin</a>, Optically Pumped UVC Photonic Crystal Surface-Emitting Laser</p> <p><b>We-B4.4 11:25-11:40:</b> <a href="#">Z. Liu</a>, Machine learning design for UVC light-emitting diodes by stacked XGBoost/LightGBM</p> <p><b>We-B4.5 11:40-11:55:</b> <a href="#">M. O'Donovan</a>, Impact of alloy disorder on carrier transport and recombination in (Al,Ga)N-based UV-C emitters</p> <p><b>We-B4.6 11:55-12:10:</b> <a href="#">U. Hansen</a>, Maximizing Light Output of DUV LEDs using Miniaturized Mirrors</p> <p><b>We-B4.7 12:10-12:25:</b> <a href="#">J. Hopfner</a>, Unravelling carrier transport in far-UVC LEDs by temperature dependent electroluminescence measurements</p>
12:30 – 13:30	<b>Lunch / Poster session</b>	
13:30 – 15:30	<p style="text-align: center;"><b>A5 Oxides</b></p> <p><b>We-A5.1 13:30-13:55:</b> <a href="#">X. Li</a>, Ga<sub>2</sub>O<sub>3</sub> research from thermal-induced growth, photodetectors, to integrated circuits</p> <p><b>We-A5.2 13:55-14:20:</b> <a href="#">A. Osinsky</a>, Growth of high purity and doped β-Ga<sub>2</sub>O<sub>3</sub> films using MOCVD</p> <p><b>We-A5.3 14:20-14:35:</b> <a href="#">M. Bickermann</a>, Gallium Oxide Bulk Crystals Prepared by the Czochralski Method, (100) Substrates, and Homoepitaxy Results</p> <p><b>We-A5.4 14:35-14:50:</b> <a href="#">D. Rogers</a>, Zinc Oxide Based Electronics &amp; Photonics: Existing &amp; Emergent Applications</p> <p><b>We-A5.5 14:50-15:05:</b> <a href="#">B. Bernhardt</a>, Energies and Orientations of the Fundamental Direct Optical Transitions in β-Ga<sub>2</sub>O<sub>3</sub></p> <p><b>We-A5.6 15:05-15:20:</b> <a href="#">H. Teisseyre</a>, Is SCAM a promising oxide material, or a scam?</p> <p><b>We-A5.7 15:20-15:35:</b> <a href="#">R-H. Horng</a>, Material Properties of n-type β-Ga<sub>2</sub>O<sub>3</sub> heteroepilayers with In-Situ Doping Grown on Sapphire by Metalorganic Chemical Vapor Deposition</p>	<p style="text-align: center;"><b>B5 WBG Phys./Applic.</b></p> <p><b>We-B5.1 13:30-13:55:</b> <a href="#">K. Sakowski</a>, Numerical simulations of AlGa<sub>N</sub> heterostructures with polarization-doping</p> <p><b>We-B5.2 13:55-14:20:</b> <a href="#">L. Van Deurzen</a>, Excitonic luminescence in homoepitaxial N-polar AlN grown on bulk substrates</p> <p><b>We-B5.3 14:20-14:45:</b> <a href="#">A. Khan</a>, Progress and Challenges of Transparent AlGa<sub>N</sub>-based UVB LEDs</p> <p><b>We-B5.4 14:45-15:00:</b> <a href="#">N. Declercq</a>, Ultraviolet light used in a historical case study of 1639</p> <p><b>We-B5.5 15:00-15:15:</b> <a href="#">E. Nogales</a>, Gallium oxide temperature-dependent refractive index and Cr doped β-Ga<sub>2</sub>O<sub>3</sub> nanowires as thermometers</p>
15:30 – 16:00	<b>Coffee break</b>	
16:00 – 17:45	<p style="text-align: center;"><b>A6 WBG Phys./Applic.</b></p> <p><b>We-A6.1 16:00-16:25:</b> <a href="#">R. Kudrawiec</a>, Studies of the electric field distribution in III-N heterostructures and the position of the Fermi level at the van der Waals/III-N interface by contactless electroreflectance in UV</p> <p><b>We-A6.2 16:25-16:50:</b> <a href="#">W. Miller</a>, Growth kinetics of AlN and AlGa<sub>N</sub> deposition on AlN(0001): A kinetic Monte Carlo Study</p> <p><b>We-A6.3 16:50-17:15:</b> <a href="#">J. Ruschel</a>, Degradation effects - Similarities and differences of UV LEDs with different wavelengths</p> <p><b>We-A6.4 17:15-17:30:</b> <a href="#">S. Schmult</a>, Highly UV-sensitive AlGa<sub>N</sub>/Ga<sub>N</sub> Heterostructures grown by MBE</p> <p><b>We-A6.5 17:30-17:45:</b> <a href="#">A. Srivastava</a>, Electrical Characteristics of p-BN/n-AlGa<sub>N</sub> Heterostructures</p>	<p style="text-align: center;"><b>B6 UV emitters</b></p> <p><b>We-B6.1 16:00-16:25:</b> <a href="#">J. Yan</a>, Deep-ultraviolet light-emitting diodes integrated with h-B(Al)N</p> <p><b>We-B6.2 16:25-16:40:</b> <a href="#">Z. Liu</a>, Investigation of novel multi-wavelength and broadband AlGa<sub>N</sub>-based UV light emitting diodes employing grading transition layers</p> <p><b>We-B6.3 16:40-16:55:</b> <a href="#">R. He</a>, Monolithically integrated AlGa<sub>N</sub>-based ultraviolet-C photonic chips for solar-blind communications</p> <p><b>We-B6.4 16:55-17:10:</b> <a href="#">F. Nippert</a>, Carrier dynamics in 230nm-emitting AlGa<sub>N</sub> quantum wells</p> <p><b>We-B6.5 17:10-17:25:</b> <a href="#">T. Guillet</a>, Ridge Ga<sub>N</sub> polariton lasers: short lasers for on-chip integration</p> <p><b>We-B6.6 17:25-17:40:</b> <a href="#">L. Valera</a>, M-plane AlGa<sub>N</sub> digital alloy for microwire UV-B LEDs</p>
19:00 – 23:00	<b>Banquet</b>	

## Thursday June 8<sup>th</sup>

08:30 – 10:00	<b>PLENARY SESSION 3</b>	
	<p><b>Th-PS3.1</b> 08:30-09:15: <a href="#">A. Allerman</a>, AlGaN Alloys for Next Generation Power Electronics</p> <p><b>Th-PS3.2</b> 09:15-10:00: <a href="#">M. Kneissl</a>, Perspectives of AlGaN-based DUV LEDs and their applications</p>	
10:00 – 10:30	<b>Coffee break</b>	
10:30 – 12:30	<p style="text-align: center;"><b>A7 2D/Nano</b></p> <p><b>Th-A7.1</b> 10:30-10:55: <a href="#">S. Sundaram</a>, Layered Boron Nitride for deep UV optoelectronics</p> <p><b>Th-A7.2</b> 10:55-11:10: <a href="#">E. Vuillermet</a>, Surface nano-structuration of 4H-SiC by controlled high-temperature annealing</p> <p><b>Th-A7.3</b> 11:10-11:25: <a href="#">S. Novikov</a>, High-temperature molecular beam epitaxy of hexagonal boron nitride and hBN-graphene-hBN lateral heterostructures</p> <p><b>Th-A7.4</b> 11:25-11:40: <a href="#">N. Gao</a>, Enhancing deep-UV sub-250 nm light emission based on truncated pyramid AlN/GaN nanostructure with fine-tuned multiple facets</p> <p><b>Th-A7.5</b> 11:40-11:55: <a href="#">R. Vermeersch</a>, Shallow donors and DX states in AlN Nanowires</p> <p><b>Th-A7.6</b> 11:55-12:10: <a href="#">L. Valera</a>, Wire-based UV-<math>\mu</math>LED using GaN and AlN microwires as template</p> <p><b>Th-A7.7</b> 12:10-12:25: <a href="#">Z. Liu</a>, Transferable Ga<sub>2</sub>O<sub>3</sub> Membrane Exfoliated from Muscovite Mica Platform for Vertical Electronics</p>	<p style="text-align: center;"><b>B7 UV emitters</b></p> <p><b>Th-B7.1</b> 10:30-10:55: <a href="#">A. Haglund</a>, Pushing VCSELs to the ultraviolet</p> <p><b>Th-B7.2</b> 10:55-11:10: <a href="#">S. Huang</a>, Deep-UV distributed Bragg reflectors with 93% reflectivity for low threshold lasers</p> <p><b>Th-B7.3</b> 11:10-11:25: <a href="#">G. Cardinali</a>, Single-mode operation of optically pumped UVB VCSELs enabled by circular surface structures</p> <p><b>Th-B7.4</b> 11:25-11:40: <a href="#">A. Kaminska</a>, Emission properties of GaN/AlN and AlGaN/AlN polar multi-quantum wells – experimental and ab initio study</p> <p><b>Th-B7.5</b> 11:40-11:55: <a href="#">A. Zaiter</a>, Growth of (Al, Ga)N Quantum Dots on h-BN and Exfoliation Processes towards the Fabrication of Flexible Efficient UV-C LEDs</p> <p><b>Th-B7.6</b> 11:55-12:10: <a href="#">R. Zhang</a>, AlGaN multiple quantum wells regrown on N-polar AlN/4H-SiC template fabricated by sputtering and high temperature annealing</p> <p><b>Th-B7.7</b> 12:10-12:25: <a href="#">N. Maeda</a>, Current-induced p-type activation of Mg-doped and highly Al compositional (x &gt; 0.8) AlGaN observed during initial energization of 220 nm band far-UVC LEDs <i>(To be confirmed)</i></p>
12:30 – 13:30	<b>Lunch / Poster session</b>	
13:30 – 15:30	<p style="text-align: center;"><b>A8 Oxides</b></p> <p><b>Th-A8.1</b> 13:30-13:55: <a href="#">M. Liao</a>, Diamond-based photodetector</p> <p><b>Th-A8.2</b> 13:55-14:20: <a href="#">K. Kaneko</a>, Germanium dioxide (GeO<sub>2</sub>) as a new power device material</p> <p><b>Th-A8.3</b> 14:20-14:35: <a href="#">C-Y Huang</a>, <math>\beta</math>-Ga<sub>2</sub>O<sub>3</sub> MOSFETs electrical characteristic study of various etching depths grown on sapphire substrate by MOCVD</p> <p><b>Th-A8.4</b> 14:35-14:50: <a href="#">B. Mendez</a>, Luminescence of doped Ga<sub>2</sub>O<sub>3</sub> nanowires</p> <p><b>Th-A8.5</b> 14:50-15:05: <a href="#">M. Narayanan</a>, Ga<sub>2</sub>O<sub>3</sub>: Examining electrical conduction and the role of oxygen vacancies</p> <p><b>Th-A8.6</b> 15:05-15:20: <a href="#">D. Maestre</a>, Elongated micro- and nanostructures formed by Ni and Mn oxides synthesized by a vapor solid method</p>	<p style="text-align: center;"><b>B8 AlGaN/AlN</b></p> <p><b>Th-B8.1</b> 13:30-13:55: <a href="#">R. Dupuis</a>, Improved Yield and Performance of III-N Ultraviolet Avalanche Photodiodes via Ion Implantation</p> <p><b>Th-B8.2</b> 13:55-14:10: <a href="#">S. Graupeter</a>, UVC LEDs emitting at 265nm grown on strain engineered HTA-AlN/sapphire templates with different offcut angles</p> <p><b>Th-B8.3</b> 14:10-14:25: <a href="#">L. Peters</a>, Revising the Role of Carbon Impurities in Aluminum Nitride</p> <p><b>Th-B8.4</b> 14:25-14:40: <a href="#">A. Klump</a>, UV Absorption Spectroscopy for the Quantification of Impurities in PVT-AlN Bulk Crystals</p> <p><b>Th-B8.5</b> 14:40-14:55: <a href="#">K. Haberland</a>, In-situ growth control during MOVPE of far-UV-C LED structures with optical metrology</p> <p><b>Th-B8.6</b> 14:55-15:20: <a href="#">X. Wang</a>, High performance AlGaN-based UVC- and UVB-LEDs on nano patterned sapphire substrate <i>(To be confirmed)</i></p>
15:30 – 16:00	<b>Coffee break</b>	
16:00 – 17:00	<p style="text-align: center;"><b>AB9 AlGaN/AlN</b></p> <p><b>Th-AB9.1</b> 16:00-16:15: <a href="#">J. Canas</a>, AlGaN/AlN quantum dots: Growth optimization for electron-beam pumped deep-UV emitters</p> <p><b>Th-AB9.2</b> 16:15-16:30: <a href="#">C. Manz</a>, Improvements in MOCVD-growth of AlGaN-based solar-blind photodetectors</p> <p><b>Th-AB9.3</b> 16:30-16:45: <a href="#">I. Prozhev</a>, Electrical compensation in Al rich Si-doped 90% AlGaN determined by positron annihilation and X-ray absorption spectroscopy</p> <p><b>Th-AB9.4</b> 16:45-17:00: <a href="#">J. Wang</a>, Reduction of threading dislocations in heteroepitaxial AlN films by extrinsic supersaturated vacancies engineering <i>(To be confirmed)</i></p>	
17:00 – 17:45	<b>Late News</b>	
17:45 – 18:15	<b>Closing</b>	